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(71) Applicant: **YANGTZE MEMORY TECHNOLOGIES CO., LTD.** [CN/CN]; No. 88 Weilai 3rd Road, East Lake High-tech Development Zone, Wuhan, Hubei 430000 (CN).

(72) Inventors: **DU, Zhichao**; No. 88 Weilai 3rd Road, East Lake High-tech Development Zone, Wuhan, Hubei 430000 (CN). **WANG, Yu**; No. 88 Weilai 3rd Road, East Lake High-tech Development Zone, Wuhan, Hubei 430000 (CN). **SONG, Daesik**; No. 88 Weilai 3rd Road, East Lake High-tech Development Zone, Wuhan, Hubei 430000 (CN). **HOU, Xu**; No. 88 Weilai 3rd Road, East Lake High-

tech Development Zone, Wuhan, Hubei 430000 (CN). **LI, Danyang**; No. 88 Weilai 3rd Road, East Lake High-tech Development Zone, Wuhan, Hubei 430000 (CN).

(74) Agent: **NTD UNIVATION INTELLECTUAL PROPERTY AGENCY LTD.**; 10th Floor, Tower C, Beijing Global Trade Center, 36 North Third Ring Road East, Dongcheng District, Beijing 100013 (CN).

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(54) Title: MEMORY DEVICES AND METHODS FOR FORMING THE SAME

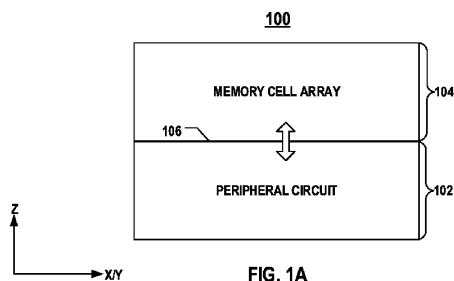


FIG. 1A

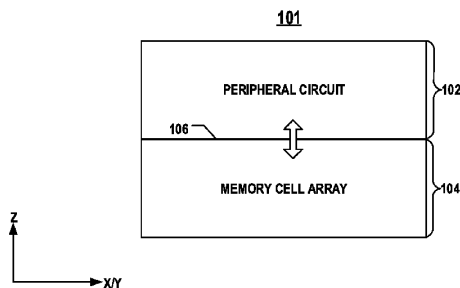


FIG. 1B

(57) Abstract: A memory device includes a memory array structure and a peripheral structure. The memory array structure includes at least one memory bank, and each memory bank includes a plurality of memory blocks. The peripheral structure includes a word line driver circuit and a sense amplifier circuit. A first area including the word line driver circuit and the sense amplifier circuit at least partially overlaps a second area including a memory block in a plan view of the memory device.

[Continued on next page]

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